

GaAs-IR-Lumineszenzdioden-Zeilen

GaAs Infrared Emitter Arrays

Lead (Pb) Free Product - RoHS Compliant

LD 260

LD 262 ... LD 269



Wesentliche Merkmale

- GaAs-IR-Lumineszenzdiode
- Zeilenbauform, lieferbar von 2 bis 10 Emittier pro Zeile
- Farbe: transparent
- Hohe Zuverlässigkeit
- Gruppiert lieferbar
- Gehäusegleich mit BPX 80-Serie
- Miniatur-Gehäuse

Anwendungen

- Miniaturlichtschranken für Gleich- und Wechsellichtbetrieb
- Barcodeleser
- Industrieelektronik
- „Messen/Steuern/Regeln“
- Sensorik
- Drehzahlsteuerung

Features

- GaAs infrared emitting diode
- Leadframe arrays, available from 2 to 10 Emitters per array
- Colour: transparent
- High reliability
- Available in bins
- Same package as BPX 80 series
- Miniature package

Applications

- Miniature photointerrupters
- Barcode readers
- Industrial electronics
- For control and drive circuits
- Sensor technology
- Speed controller

Typ Type	ired pro Zeile per Row	Bestellnummer Ordering Code	Strahlstärkegruppierung ¹⁾ ($I_F = 50 \text{ mA}$, $t_p = 20 \text{ ms}$) Radiant intensity grouping ¹⁾ $I_e \text{ (mW/sr)}$
LD 262	2	Q62703Q0070	> 2.5 (typ. 5)
LD 263	3	Q62703Q0071	
LD 264	4	Q62703Q0072	
LD 265	5	Q62703Q0073	
LD 266	6	Q62703Q0074	
LD 267	7	Q62703Q0075	
LD 268	8	Q62703Q0076	
LD 269	9	Q62703Q0077	
LD 260	10	Q62703Q0078	

¹⁾ gemessen bei einem Raumwinkel $\Omega = 0.01 \text{ sr}$ / measured at a solid angle of $\Omega = 0.01 \text{ sr}$

Grenzwerte ($T_A = 25\text{ °C}$)**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 80	°C
Sperrschichttemperatur Junction temperature	T_j	80	°C
Sperrspannung Reverse voltage	V_R	5	V
Durchlassstrom Forward current	I_F	50	mA
Stoßstrom, $\tau \leq 10\text{ }\mu\text{s}$, $D = 0$ Surge current	I_{FSM}	1.6	A
Verlustleistung Power dissipation	P_{tot}	70	mW
Wärmewiderstand Thermal resistance	R_{thJA} R_{thJL}	750 650	K/W K/W

Kennwerte ($T_A = 25\text{ °C}$)**Characteristics**

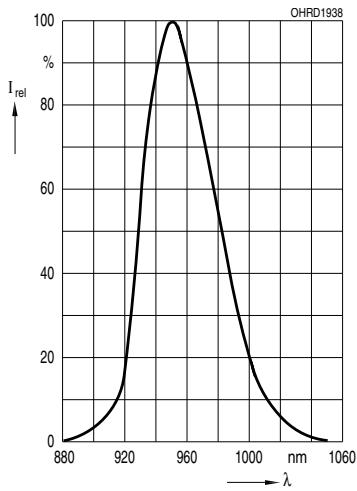
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 50\text{ mA}$, $t_p = 20\text{ ms}$	λ_{peak}	950	nm
Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} $I_F = 50\text{ mA}$, $t_p = 20\text{ ms}$	$\Delta\lambda$	55	nm
Abstrahlwinkel Half angle	φ	± 15	Grad deg.
Aktive Chipfläche Active chip area	A	0.25	mm ²
Abmessungen der aktiven Chipfläche Dimension of the active chip area	$L \times B$ $L \times W$	0.5×0.5	mm ²
Abstand Chipoberfläche bis Linsenscheitel Distance chip surface to lens top	H	1.3 ... 1.9	mm

Kennwerte ($T_A = 25\text{ °C}$)**Characteristics** (cont'd)

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei $I_F = 50\text{ mA}$, $R_L = 50\text{ }\Omega$ Switching times, I_e from 10% to 90% and from 90% to 10%, $I_F = 50\text{ mA}$, $R_L = 50\text{ }\Omega$	t_r, t_f	1	μs
Kapazität, $V_R = 0\text{ V}$ Capacitance	C_o	40	pF
Durchlassspannung, $I_F = 50\text{ mA}$, $t_p = 20\text{ }\mu\text{s}$ Forward voltage	V_F	1.25 (≤ 1.4)	V
Sperrstrom, $V_R = 5\text{ V}$ Reverse current	I_R	0.01 (≤ 1)	μA
Gesamtstrahlungsfluss, $I_F = 50\text{ mA}$, $t_p = 20\text{ ms}$ Total radiant flux	Φ_e	9	mW
Temperaturkoeffizient von I_e bzw. Φ_e , $I_F = 50\text{ mA}$ Temperature coefficient of I_e or Φ_e , $I_F = 50\text{ mA}$	TC_I	- 0.55	%/K
Temperaturkoeffizient von V_F , $I_F = 50\text{ mA}$ Temperature coefficient of V_F , $I_F = 50\text{ mA}$	TC_V	- 1.5	mV/K
Temperaturkoeffizient von λ_{peak} , $I_F = 50\text{ mA}$ Temperature coefficient of λ_{peak} , $I_F = 50\text{ mA}$	TC_λ	0.3	nm/K
Strahlstärke, $I_F = 50\text{ mA}$, $t_p = 20\text{ ms}$ Radiant intensity	I_e	typ. 5 (≥ 2)	mW/sr

Relative Spectral Emission

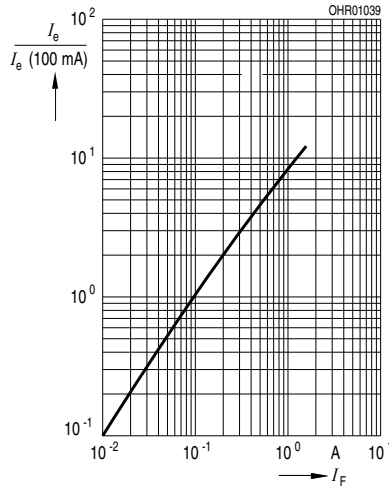
$$I_{\text{rel}} = f(\lambda)$$



Radiant Intensity

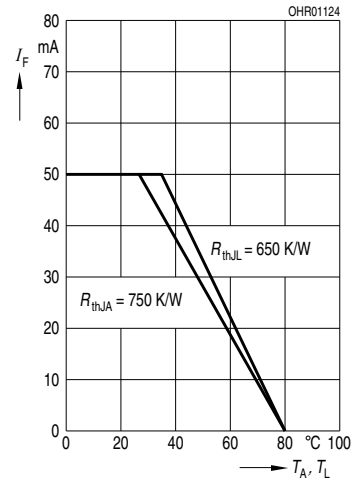
$$\frac{I_e}{I_e 100 \text{ mA}} = f(I_F)$$

Single pulse, $t_p = 20 \mu\text{s}$



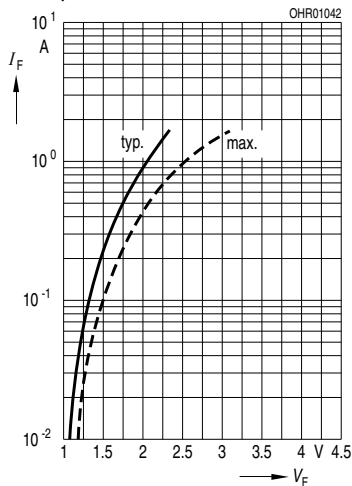
Max. Permissible Forward Current

$$I_F = f(T_A)$$



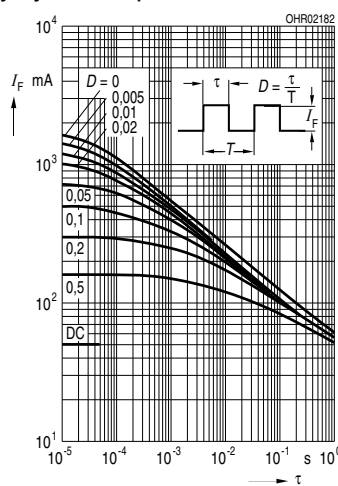
Forward Current

$$I_F = f(V_E), \text{ single pulse, } t_p = 20 \mu\text{s}$$



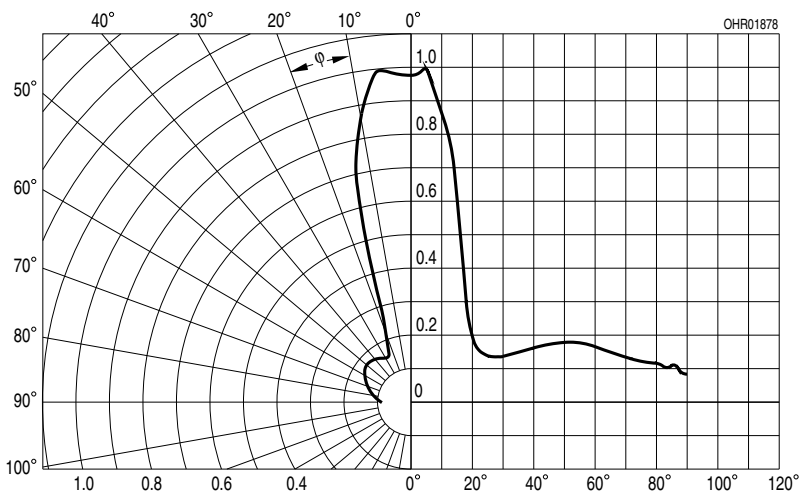
Permissible Pulse Handling

$$I_F = f(\tau), T_C = 25^\circ\text{C}, \text{ duty cycle } D = \text{parameter}$$

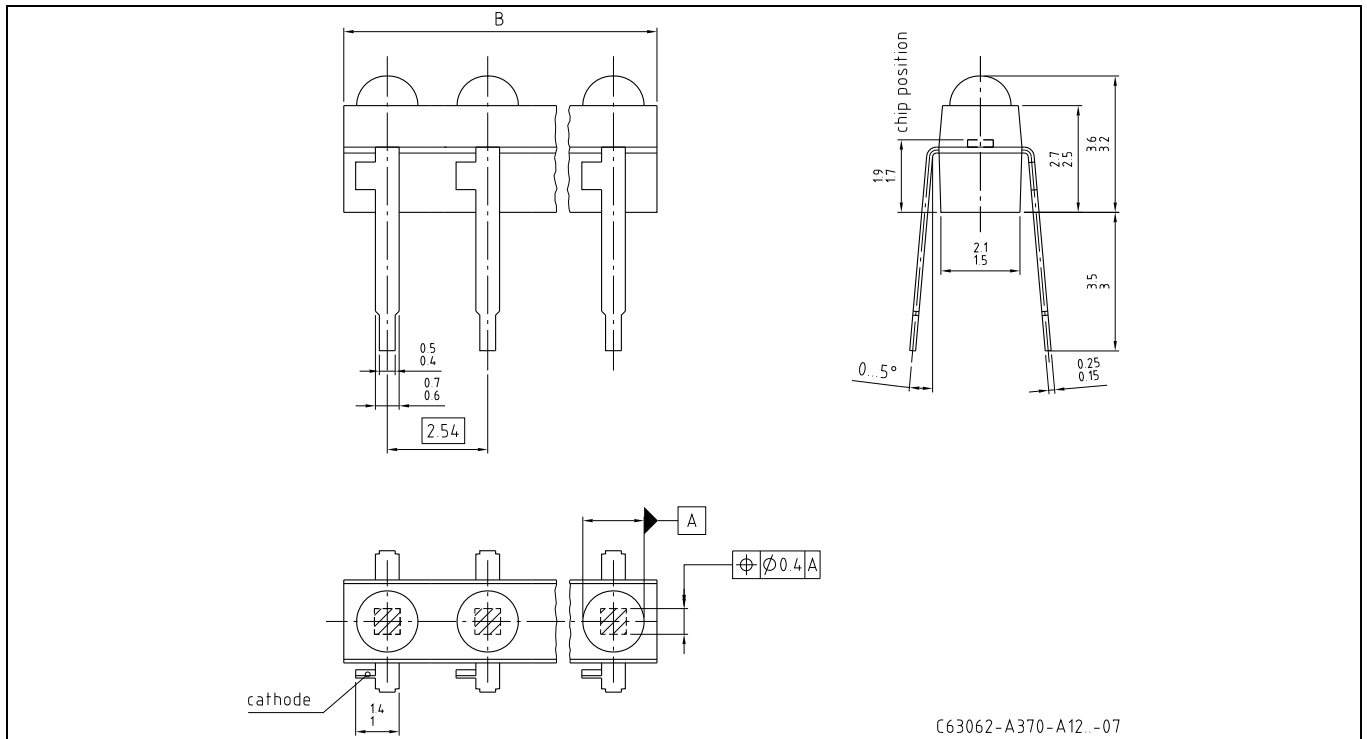


Radiation Characteristics

$$I_{\text{rel}} = f(\varphi)$$



Maßzeichnung **Package Outlines**

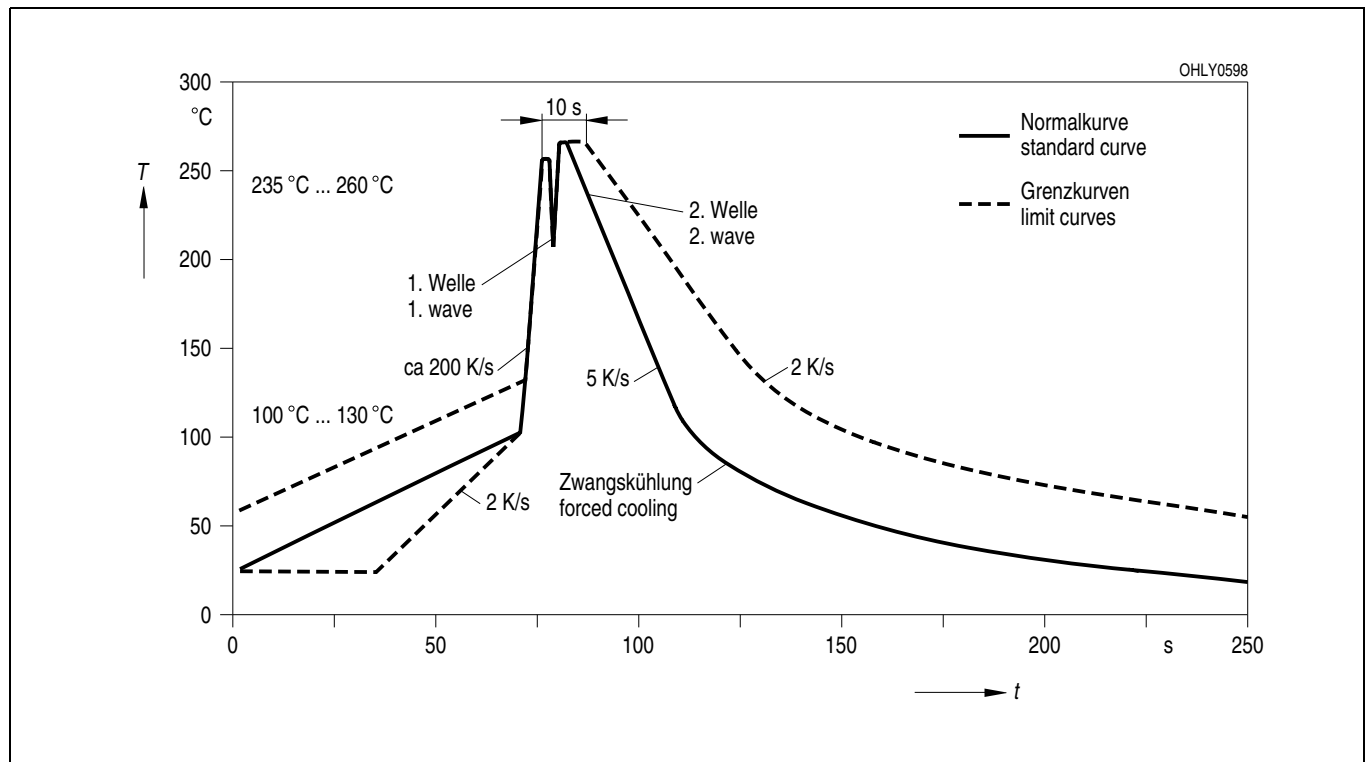


Maße in mm / Dimensions in mm.

Type	IRET pro Zeile	Maß „B“
Type	IRET per Row	Dimension “B”
LD 262	2	4.5 ... 4.9
LD 263	3	7.0 ... 7.4
LD 264	4	9.6 ... 10.0
LD 265	5	12.1 ... 12.5
LD 266	6	14.6 ... 16.0
LD 267	7	17.2 ... 17.6
LD 268	8	19.7 ... 20.1
LD 269	9	22.3 ... 22.7
LD 270	10	24.8 ... 25.2

Lötbedingungen
Soldering Conditions
Wellenlöten (TTW)
TTW Soldering

(nach CECC 00802)
 (acc. to CECC 00802)



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